

# Epi - Wafer

## Undoped GaN



<b>Feature</b>	Undoped GaN Epi. Wafer Single side polished (Growth surface)
<b>Diameter</b>	2" (50.8mm)
<b>Thickness (Included substrate)</b>	~2 $\mu$ m (+/-10% std)
<b>Structure</b>	<b>u-GaN</b> / Sapphire substrate



GaN on Sapphire Wafer

### Characteristics (at 25°C)

Parameter		Typ.	Test Conditions
PL measurement	Peak wavelength	362nm $\pm$ 2nm	Etamax PLATO Laser : 266nm
	Uniformity STD	<3%	
	FWHM	<10nm	
	FWHM STD	<3%	
Thickness	Thickness	~2 $\mu$ m (+/-10% std)	
	Thickness STD	<10%	
XRD	(002)	<350 arcsec	Panalytical HRXRD
	(102)	<450 arcsec	
Hall	Carrier Concentration	< -1 $\times$ 10 <sup>17</sup> /cm <sup>3</sup>	Accent HL5500
	Mobility	>200 cm <sup>2</sup> /V-sec	
Doping material	Si	N/A	-
	Mg	N/A	

### Normalized Single Spectrum(300 ~ 700nm)

